



InGaAs PIN photodiodes

G12183 series

Long wavelength type (cutoff wavelength: 2.55 to 2.6 μm)

■ Features

- Cutoff wavelength: 2.55 to 2.6 μm
- Low cost
- Photosensitive area: ϕ 0.3 to ϕ 3 mm
- Low noise
- High sensitivity
- High reliability
- High-speed response
- High short-wavelength sensitivity
(G12183-210KA-03): 0.4 A/W ($\lambda=900$ nm)

■ Applications

- Optical power meters
- Gas analysis
- Moisture meters
- NIR (near infrared) photometry

■ Options

- Amplifier for InGaAs PIN photodiode C4159-03
- Heatsink for two-stage TE-cooled type A3179
- Heatsink for two-stage TE-cooled type A3179-01
(excluding G12183-210KA-03)
- Temperature controller for TE-cooled type C1103-04

■ Structure

Type no.	Dimensional outline/ Window material*1	Package	Cooling	Photosensitive area (mm)	
G12183-003K	(1)/K	TO-18	Non-cooled	ϕ 0.3	
G12183-005K				ϕ 0.5	
G12183-010K		TO-5		ϕ 1	
G12183-020K				ϕ 2	
G12183-030K				ϕ 3	
G12183-103K	(3)/K	TO-8	One-stage TE-cooled	ϕ 0.3	
G12183-105K				ϕ 0.5	
G12183-110K				ϕ 1	
G12183-120K				ϕ 2	
G12183-130K				ϕ 3	
G12183-203K	(4)/K	TO-8	Two-stage TE-cooled	ϕ 0.3	
G12183-205K				ϕ 0.5	
G12183-210K				ϕ 1	
G12183-220K				ϕ 2	
G12183-230K				ϕ 3	
G12183-210KA-03	(5)/K	TO-66	Two-stage TE-cooled	ϕ 1	

*1: K=borosilicate glass

The G12183 series may be destroyed or deteriorated by static electricity. Use caution when handling.

▪ Absolute maximum ratings (Ta=25 °C unless otherwise noted)

Type no.	Thermistor power dissipation Pd_th (mW)	Allowable TE-cooler current I _{TE} max (A)	Allowable TE-cooler voltage V _{TE} max (V)	Reverse voltage V _R max (V)	Operating temperature* ² T _{opr} (°C)	Storage temperature* ² T _{stg} (°C)
G12183-003K	-	-	-	-	-40 to +85	-55 to +125
G12183-005K						
G12183-010K						
G12183-020K						
G12183-030K						
G12183-103K						
G12183-105K						
G12183-110K		1.5	1.0	1		
G12183-120K						
G12183-130K						
G12183-203K					-40 to +70* ³	-55 to +85
G12183-205K						
G12183-210K		1.0	1.2			
G12183-220K						
G12183-230K						
G12183-210KA-03				0.5		

*2: No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environment, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

*3: Chip temperature and package temperature

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

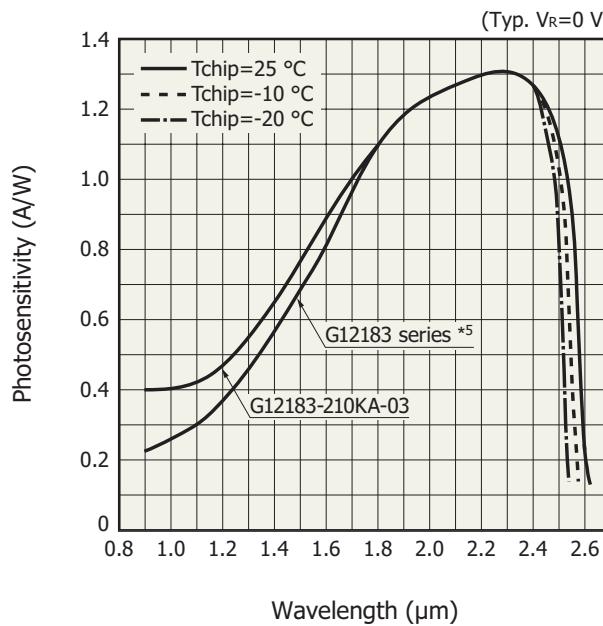
▪ Electrical and optical characteristics (Typ. unless otherwise noted)

Type no.	Measurement conditions Chip temperature T _{chip} (°C)	Thermistor resistance (+25 °C) R _{sh} (kΩ)	Thermistor B constant (-20/+25 °C) B (K)	Spectral response range λ (μm)	Peak sensitivity wavelength λ _p (μm)	Photosensitivity S λ=λ _p		Dark current I _D V _R =0.5 V		Temperature coefficient of dark current V _R =0.5 V (times/°C)			
						Min. (A/W)	Typ. (A/W)	Typ. (μA)	Max. (μA)				
G12183-003K	25	-	-	0.9 to 2.6	2.3	1	1.3	0.4	4	1.035			
G12183-005K								1	10				
G12183-010K								3	30				
G12183-020K								10	100				
G12183-030K								30	300				
G12183-103K	-10	9.0	3300	0.9 to 2.57	2.3	1	1.3	0.12	1.2	1.035			
G12183-105K								0.3	3				
G12183-110K				0.9 to 2.57				0.9	9				
G12183-120K								3	30				
G12183-130K				0.9 to 2.55				9	90				
G12183-203K	-20	9.0	3300		2.3	1	1.3	0.085	0.85	1.035			
G12183-205K								0.21	2.1				
G12183-210K								0.65	6.5				
G12183-220K								2.1	21				
G12183-230K								6	60				
G12183-210KA-03								0.05* ⁴	0.1* ⁴	1.067* ⁴			

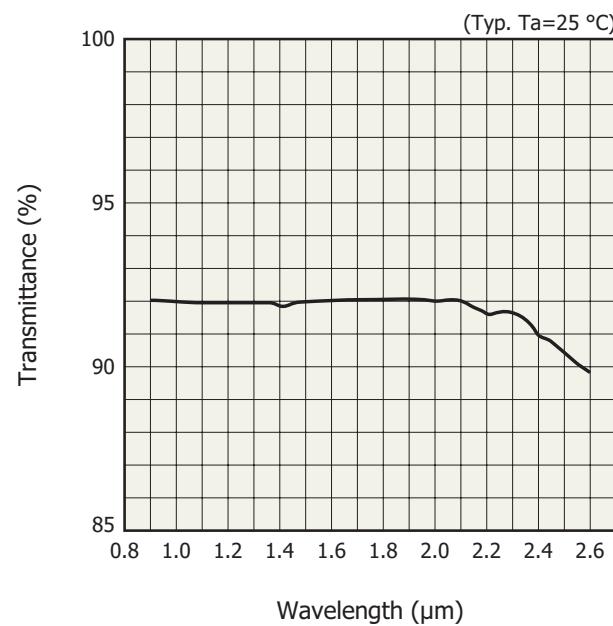
*4: V_R=10 mV

Type no.	Measurement conditions	Cutoff frequency fc		Terminal capacitance Ct		Shunt resistance Rsh		Detectivity D* $\lambda=\lambda p$		Noise equivalent power NEP $\lambda=\lambda p$	
		VR=0 V RL=50 Ω		VR=0 V f=1 MHz		VR=10 mV					
	Chip temperature Tchip (°C)	Min. (MHz)	Typ. (MHz)	Typ. (pF)	Max. (pF)	Min. (kΩ)	Typ. (kΩ)	Min. (cm·Hz ^{1/2} /W)	Typ. (cm·Hz ^{1/2} /W)	Typ. (W/Hz ^{1/2})	Max. (W/Hz ^{1/2})
G12183-003K	25	20	50	50	100	20	100	3×10^{10}	9×10^{10}	4×10^{-13}	9×10^{-13}
G12183-005K		5	20	140	300	10	50			5×10^{-13}	1.5×10^{-12}
G12183-010K		2	6	500	1000	2.8	14			1×10^{-12}	3×10^{-12}
G12183-020K		1	1.5	1800	3000	0.65	3			2×10^{-12}	5×10^{-12}
G12183-030K		0.5	0.8	4000	5000	0.25	1.4			3×10^{-12}	8×10^{-12}
G12183-103K	-10	20	70	44	100	200	1000	1×10^{11}	3×10^{11}	1×10^{-13}	3×10^{-13}
G12183-105K		5	25	120	300	100	500			1.5×10^{-13}	4.5×10^{-13}
G12183-110K		2	7	440	1000	28	140			2.5×10^{-13}	8×10^{-13}
G12183-120K		1	2	1500	3000	6.5	30			5.5×10^{-13}	2×10^{-12}
G12183-130K		0.5	0.9	3400	5000	2.8	14			8.5×10^{-13}	2.5×10^{-12}
G12183-203K	-20	20	75	40	100	400	2000	1.5×10^{11}	4.5×10^{11}	7×10^{-14}	2×10^{-13}
G12183-205K		5	28	110	300	200	1000			1×10^{-13}	3×10^{-13}
G12183-210K		2	8	400	1000	55	280			2×10^{-13}	5.5×10^{-13}
G12183-220K		1	2.3	1400	3000	13	60			4×10^{-13}	1×10^{-12}
G12183-230K		0.5	1	3200	5000	5.5	28			6×10^{-13}	2×10^{-12}
G12183-210KA-03		2	4	500	1000	100	200	2×10^{11}	4×10^{11}	2×10^{-13}	4×10^{-13}

▪ Spectral response



▪ Spectral transmittance of window material

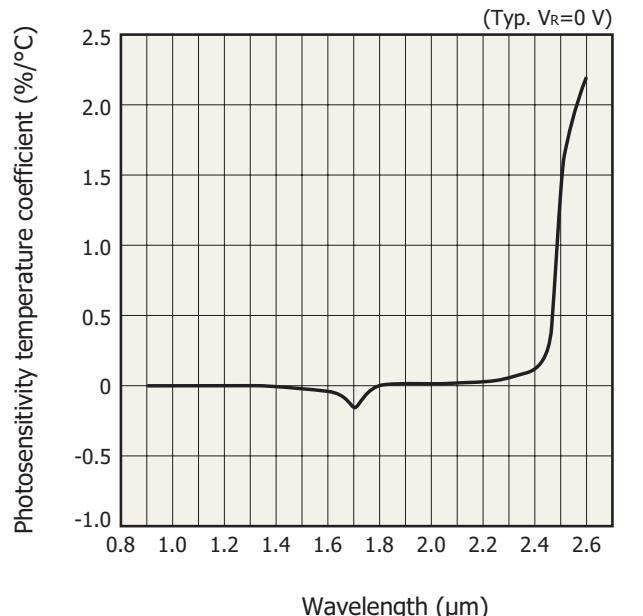


*5: Excluding G12183-210KA-03

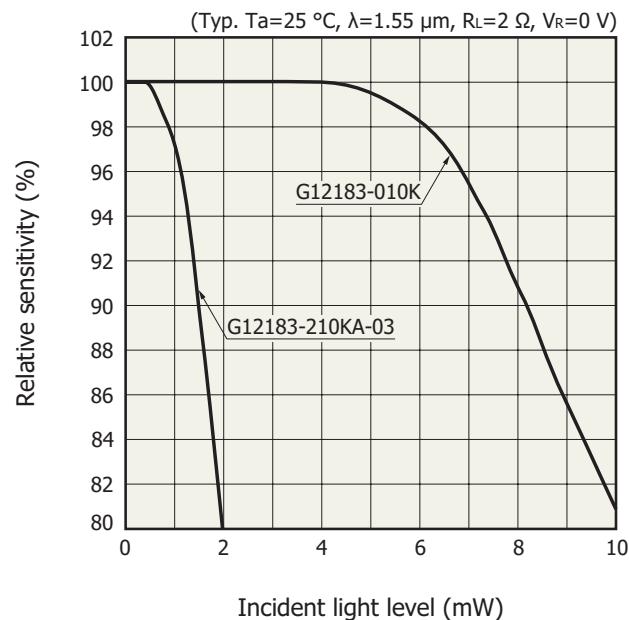
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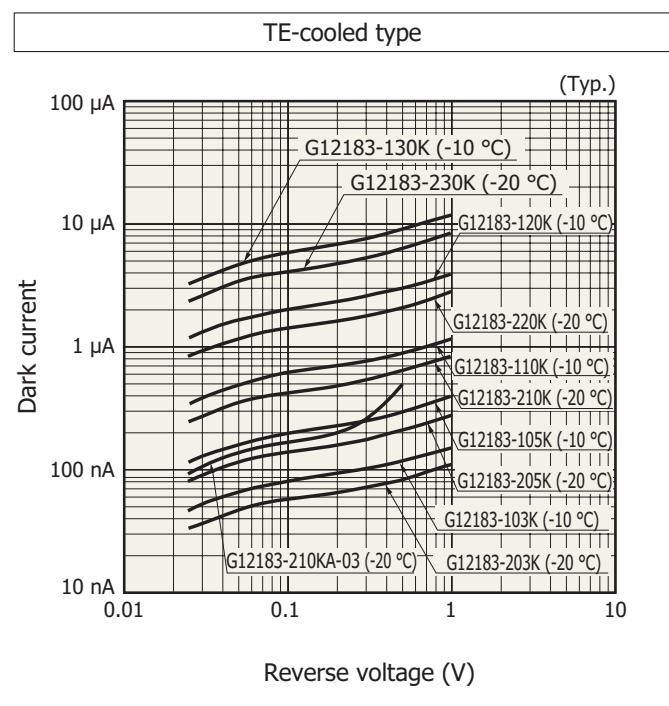
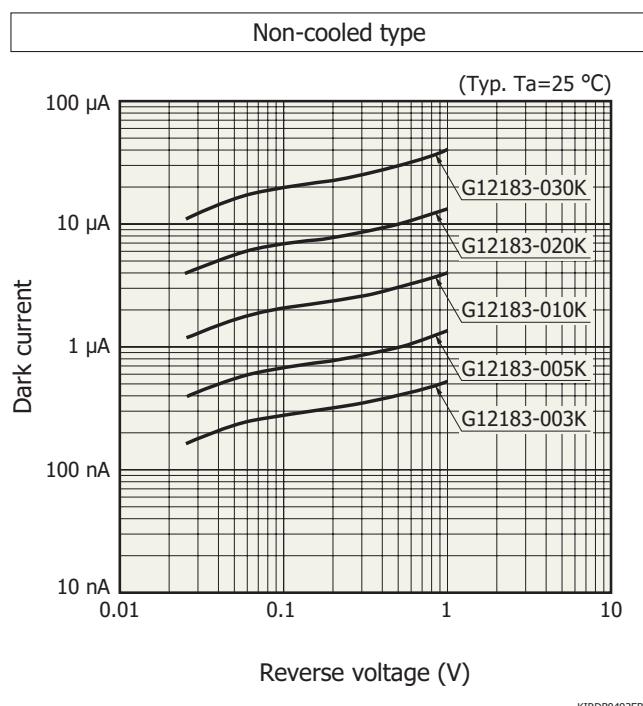
Photosensitivity temperature characteristics



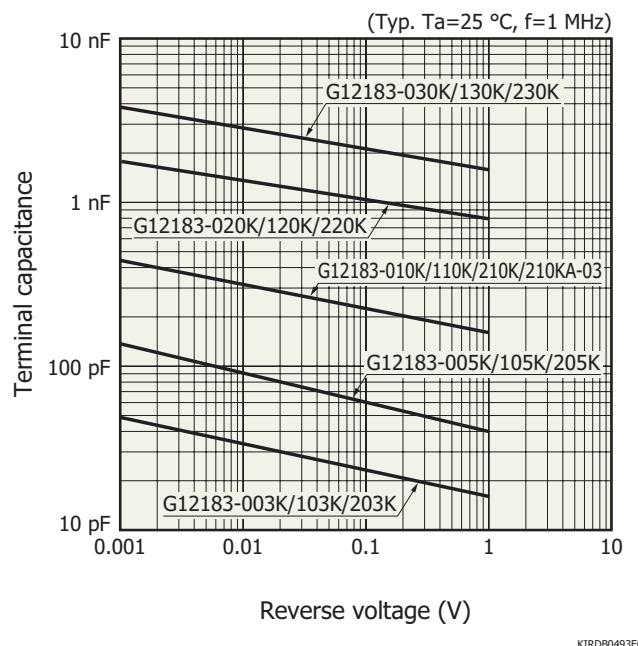
Linearity



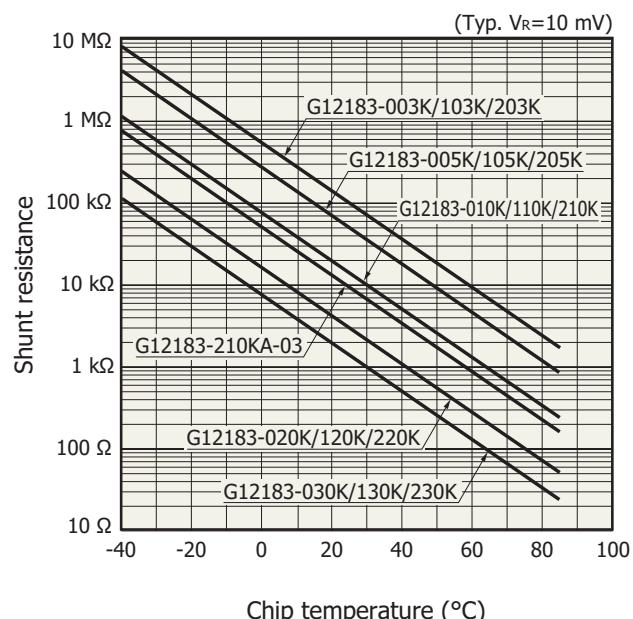
Dark current vs. reverse voltage



Terminal capacitance vs. reverse voltage

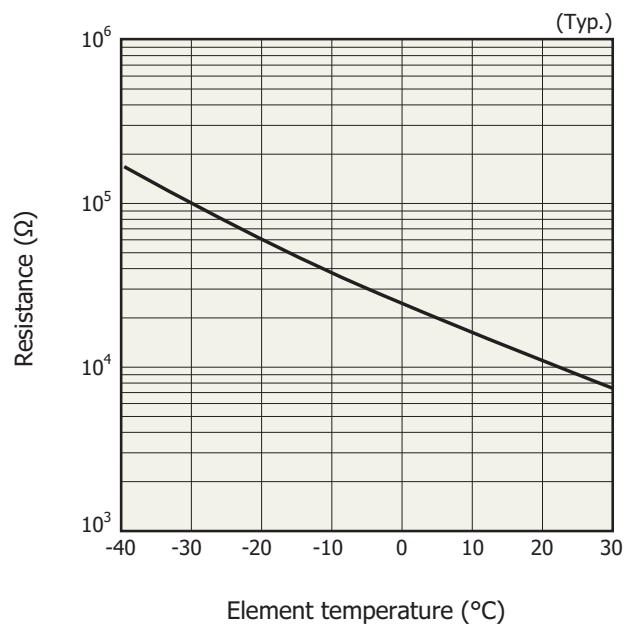


Shunt resistance vs. chip temperature

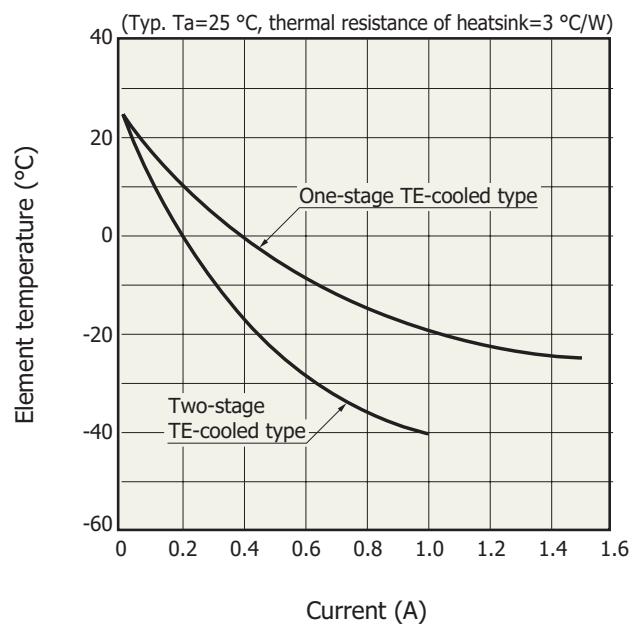


Note: The operating temperature for the one-stage TE-cooled type and two-stage TE-cooled type is up to 70 °C.

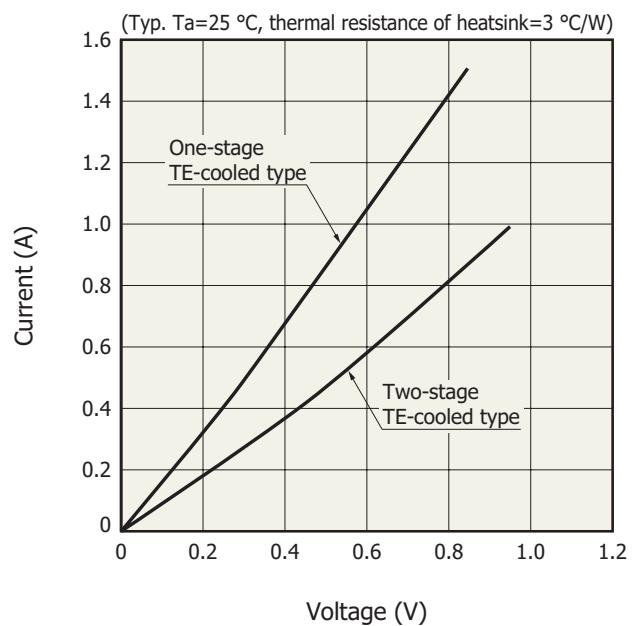
Thermistor temperature characteristics



Cooling characteristics of TE-cooler

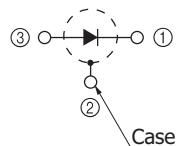
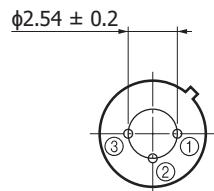
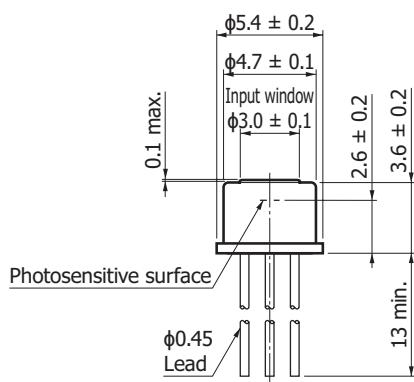


Current vs. voltage characteristics of TE-cooler



Dimensional outlines (unit: mm)

(1) G12183-003K/005K/010K

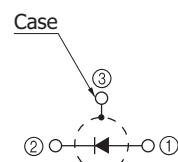
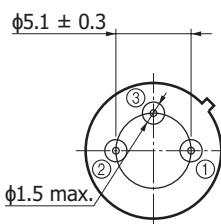
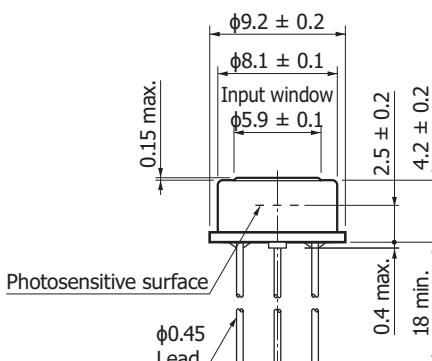


Distance from photosensitive area center to cap center

$$\begin{aligned}-0.2 \leq X \leq +0.2 \\ -0.2 \leq Y \leq +0.2\end{aligned}$$

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(2) G12183-020K/030K

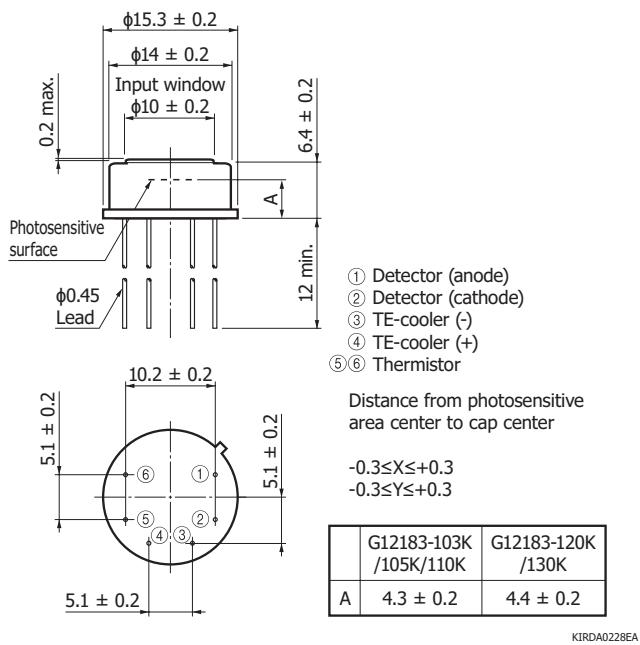


Distance from photosensitive area center to cap center

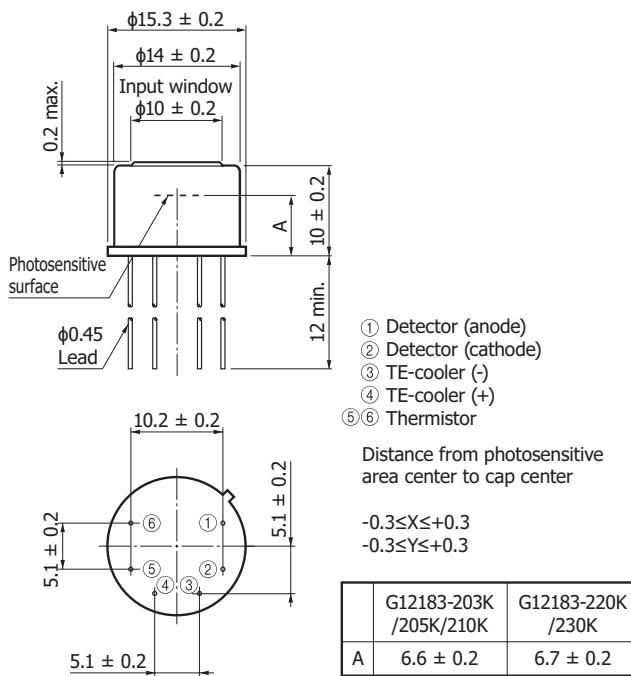
$$\begin{aligned}-0.2 \leq X \leq +0.2 \\ -0.2 \leq Y \leq +0.2\end{aligned}$$

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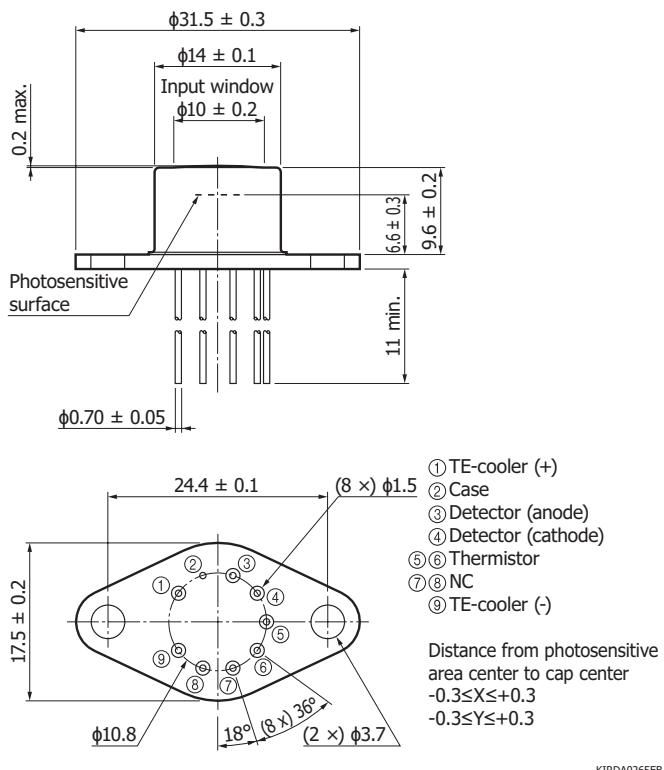
(3) G12183-103K/105K/110K/120K/130K



(4) G12183-203K/205K/210K/220K/230K



(5) G12183-210KA-03



■ Recommended soldering conditions

Solder temperature: 260 °C (10 s or less, once)

Solder the leads at a point at least 1 mm away from the package body.

Note: When you set soldering conditions, check that problems do not occur in the product by testing out the conditions in advance.

■ Related information

www.hamamatsu.com/sp/ssd/doc_en.html

■ Precautions

- Disclaimer
- Safety consideration
- Compound opto-semiconductors (photosensors, light emitters)

Information described in this material is current as of January 2021.

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